

This IC includes high-accuracy voltage detection circuits and delay circuits, and can monitor the status of 3-serial to 5-serial cell lithium-ion rechargeable batteries through small 8-pin packages.

Short-circuiting between cells makes it possible for serial connection of 3-cell to 5-cell.

■ Features

- High-accuracy voltage detection circuit for each cell

Overcharge detection voltage n	3.500 V to 4.700 V (5 mV step)	Accuracy ± 15 mV ($T_a = +25^\circ\text{C}$)
		Accuracy ± 20 mV ($T_a = -10^\circ\text{C}$ to $+60^\circ\text{C}$)
Overcharge release voltage n ^{*1}	3.100 V to 4.700 V	Accuracy ± 50 mV
Overdischarge detection voltage n	1.500 V to 3.200 V (50 mV step)	Accuracy ± 80 mV
Overdischarge release voltage n ^{*2}	1.500 V to 3.900 V (100 mV step)	Accuracy ± 100 mV
- Delay times are generated only by an internal circuit (external capacitors are unnecessary)

Overcharge detection delay time:	0.5 s, 1 s, 2 s, 4 s, 6 s, 8 s
Overdischarge detection delay time:	128 ms, 256 ms, 0.5 s, 1 s
- CO and DO pin output voltage is limited to 7.5 V max. respectively
- CO pin, DO pin output form: CMOS output, Nch open-drain output
- CO pin, DO pin output logic: Active "H", active "L"
- High-withstand voltage: Absolute maximum rating 28 V
- Wide operation voltage range: 3.6 V to 24 V
- Wide operation temperature range: $T_a = -40^\circ\text{C}$ to $+85^\circ\text{C}$
- Low current consumption

During operation (3.4 V for each cell):	7.0 μA max.
---	------------------------
- Lead-free (Sn 100%), halogen-free

*1. Overcharge release voltage = Overcharge detection voltage – Overcharge hysteresis voltage
(Overcharge hysteresis voltage can be selected from a range of 0 mV to 400 mV in 50 mV step.)

*2. Overdischarge release voltage = Overdischarge detection voltage + Overdischarge hysteresis voltage
(Overdischarge hysteresis voltage can be selected from a range of 0 mV to 700 mV in 100 mV step.)

Remark n = 1, 2, 3, 4, 5

■ Applications

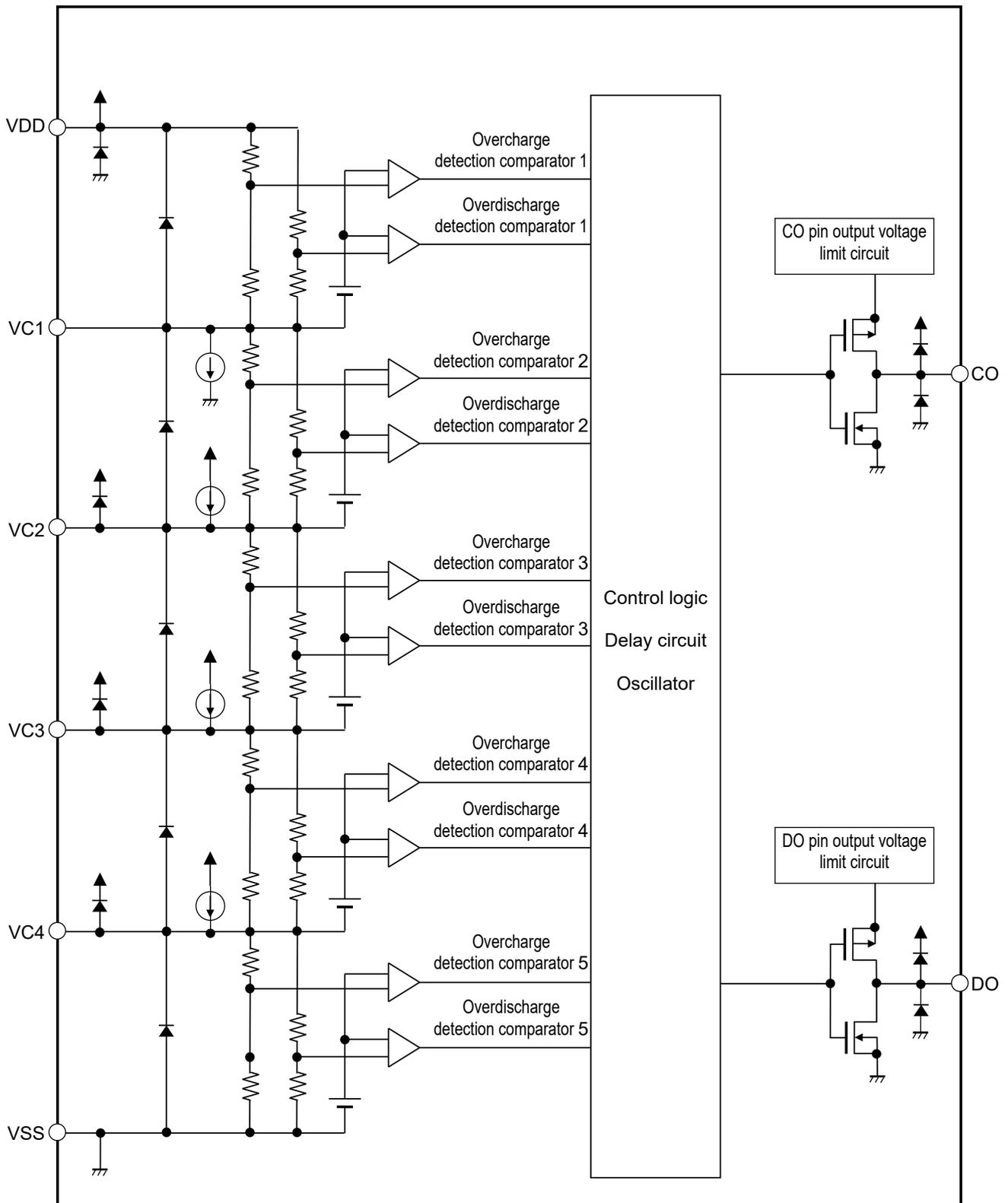
- Lithium-ion rechargeable battery pack

■ Packages

- TMSOP-8
- SNT-8A

■ **Block Diagram**

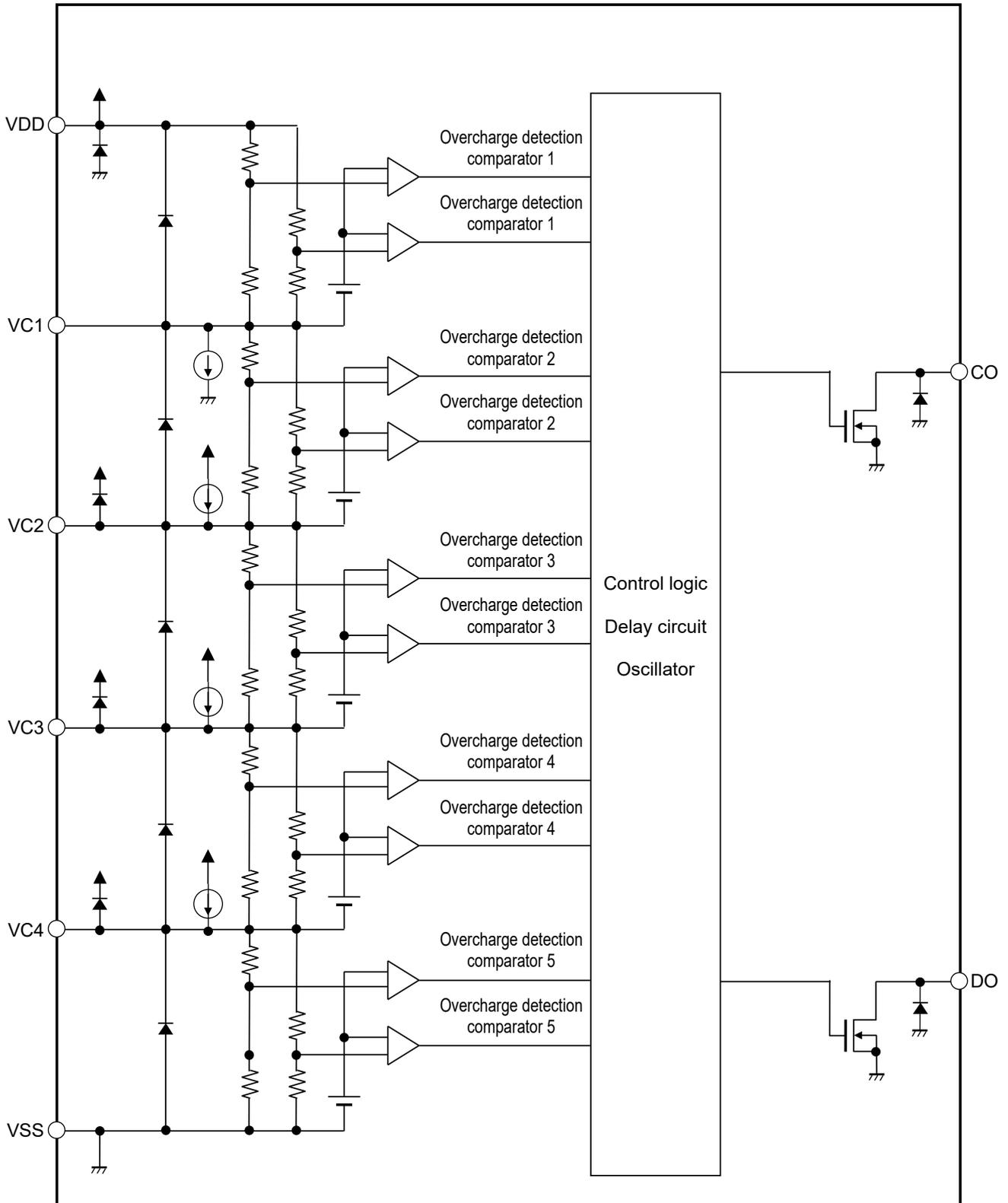
1. **CMOS output product**



Remark Diodes in the figure are parasitic diodes.

Figure 1

2. Nch open-drain output product

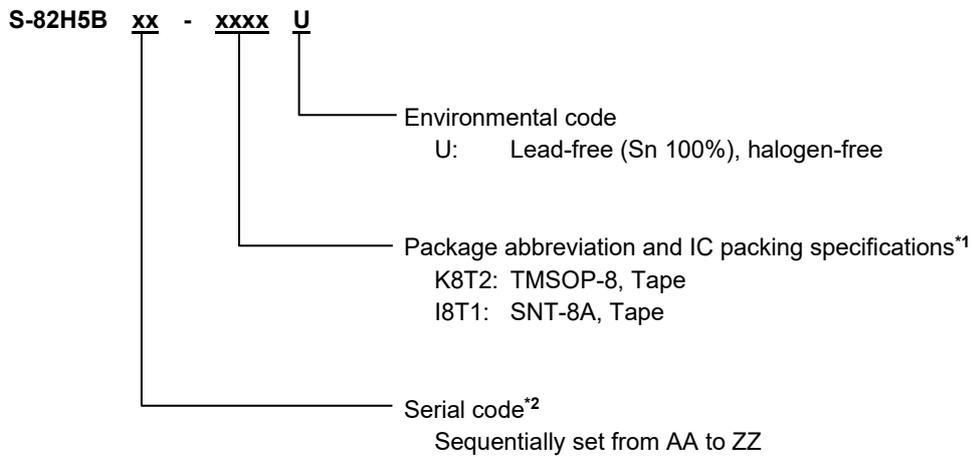


Remark Diodes in the figure are parasitic diodes.

Figure 2

■ **Product Name Structure**

1. **Product name**



*1. Refer to the tape drawing.

*2. Refer to "3. Product name list".

2. **Package**

Table 1 Package Drawing Codes

Package Name	Dimension	Tape	Reel	Land
TMSOP-8	FM008-A-P-SD	FM008-A-C-SD	FM008-A-R-SD	-
SNT-8A	PH008-A-P-SD	PH008-A-C-SD	PH008-A-R-SD	PH008-A-L-SD

BATTERY MONITORING IC FOR 3-SERIAL TO 5-SERIAL CELL PACK

Rev.1.1_00

S-82H5B Series

3. Product name list

3.1 TMSOP-8

Table 2 (1 / 2)

Product Name	Overcharge Detection Voltage [V _{CU}]	Overcharge Release Voltage [V _{CL}]	Overdischarge Detection Voltage [V _{DL}]	Overdischarge Release Voltage [V _{DU}]	Overcharge Detection Delay Time* ¹ [t _{CU}]	Overdischarge Detection Delay Time* ² [t _{DL}]
S-82H5BAA-K8T2U	4.275 V	4.225 V	2.000 V	2.200 V	1.0 s	1.0 s

Table 2 (2 / 2)

Product Name	CO Pin Output Form	CO Pin Output Logic	DO Pin Output Form	DO Pin Output Logic
S-82H5BAA-K8T2U	Nch open-drain output	Active "L"	CMOS output	Active "H"

*1. Overcharge detection delay time: 0.5 s, 1 s, 2 s, 4 s, 6 s, 8 s

*2. Overdischarge detection delay time: 128 ms, 256 ms, 0.5 s, 1 s

Remark Please contact our sales representatives for products other than the above.

■ **Pin Configuration**

1. **TMSOP-8**

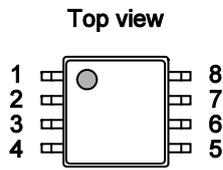


Figure 3

Table 3

Pin No.	Symbol	Description
1	VDD	Positive power supply input pin, Positive voltage connection pin of battery 1
2	VC1	Negative voltage connection pin of battery 1, Positive voltage connection pin of battery 2
3	VC2	Negative voltage connection pin of battery 2, Positive voltage connection pin of battery 3
4	VC3	Negative voltage connection pin of battery 3, Positive voltage connection pin of battery 4
5	VC4	Negative voltage connection pin of battery 4, Positive voltage connection pin of battery 5
6	VSS	Negative power supply input pin, Negative voltage connection pin of battery 5
7	DO	Overdischarge detection output pin
8	CO	Overcharge detection output pin

2. **SNT-8A**

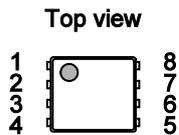


Figure 4

Table 4

Pin No.	Symbol	Description
1	VDD	Positive power supply input pin, Positive voltage connection pin of battery 1
2	VC1	Negative voltage connection pin of battery 1, Positive voltage connection pin of battery 2
3	VC2	Negative voltage connection pin of battery 2, Positive voltage connection pin of battery 3
4	VC3	Negative voltage connection pin of battery 3, Positive voltage connection pin of battery 4
5	VC4	Negative voltage connection pin of battery 4, Positive voltage connection pin of battery 5
6	VSS	Negative power supply input pin, Negative voltage connection pin of battery 5
7	DO	Overdischarge detection output pin
8	CO	Overcharge detection output pin

BATTERY MONITORING IC FOR 3-SERIAL TO 5-SERIAL CELL PACK S-82H5B Series

Rev.1.1_00

■ Absolute Maximum Ratings

Table 5

(Ta = +25°C unless otherwise specified)

Item		Symbol	Applied Pin	Absolute Maximum Rating	Unit
Input voltage between VDD pin and VSS pin		V _{DS}	VDD	V _{SS} - 0.3 to V _{SS} + 28	V
Input pin voltage		V _{IN1}	VC1	V _{DD} - 6.0 to V _{DD} + 0.3, V _{IN2} - 0.3 to V _{IN2} + 6.0	V
		V _{IN2}	VC2	V _{IN3} - 0.3 to V _{IN3} + 6.0, V _{IN3} - 0.3 to V _{DD} + 0.3	V
		V _{IN3}	VC3	V _{IN4} - 0.3 to V _{IN4} + 6.0, V _{IN4} - 0.3 to V _{DD} + 0.3	V
		V _{IN4}	VC4	V _{SS} - 0.3 to V _{SS} + 6.0, V _{SS} - 0.3 to V _{DD} + 0.3	V
Output pin voltage	CMOS output product	V _{OUT}	DO	V _{SS} - 0.3 to V _{DD} + 0.3	V
			CO	V _{SS} - 0.3 to V _{DD} + 0.3	V
	Nch open-drain output product		DO	V _{SS} - 0.3 to V _{SS} + 28	V
			CO	V _{SS} - 0.3 to V _{SS} + 28	V
Operation ambient temperature		T _{opr}	-	-40 to +85	°C
Storage temperature		T _{stg}	-	-40 to +125	°C

Caution The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

■ Thermal Resistance Value

Table 6

Items	Symbol	Condition	Min.	Typ.	Max.	Unit	
Junction-to-ambient thermal resistance*1	θ _{JA}	TMSOP-8	Board A	-	160	-	°C/W
			Board B	-	133	-	°C/W
			Board C	-	-	-	°C/W
			Board D	-	-	-	°C/W
			Board E	-	-	-	°C/W
		SNT-8A	Board A	-	211	-	°C/W
			Board B	-	173	-	°C/W
			Board C	-	-	-	°C/W
			Board D	-	-	-	°C/W
			Board E	-	-	-	°C/W

*1. Test environment: compliance with JEDEC STANDARD JESD51-2A

Remark Refer to "■ Power Dissipation" and "Test Board" for details.

■ **Electrical Characteristics**

Table 7

(Ta = +25°C unless otherwise specified)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit	Test Circuit
Detection Voltage							
Overcharge detection voltage n (n = 1, 2, 3, 4, 5)	V _{CU_n}	V1 = V2 = V3 = V4 = V5 = V _{CU} - 0.1 V	V _{CU} - 0.015	V _{CU}	V _{CU} + 0.015	V	1
		Ta = -10°C to +60°C*1, V1 = V2 = V3 = V4 = V5 = V _{CU} - 0.1 V	V _{CU} - 0.020	V _{CU}	V _{CU} + 0.020	V	1
Overcharge release voltage n (n = 1, 2, 3, 4, 5)	V _{CL_n}	-	V _{CL} - 0.050	V _{CL}	V _{CL} + 0.050	V	2
Overdischarge detection voltage n (n = 1, 2, 3, 4, 5)	V _{DL_n}	-	V _{DL} - 0.08	V _{DL}	V _{DL} + 0.08	V	2
Overdischarge release voltage n (n = 1, 2, 3, 4, 5)	V _{DU_n}	-	V _{DU} - 0.10	V _{DU}	V _{DU} + 0.10	V	2
Input Voltage							
Operation voltage between VDD pin and VSS pin	V _{DSOP}	-	3.6	-	24	V	-
Output Voltage							
CO pin voltage "H"	V _{COH}	CMOS output product	5.0	6.0	7.5	V	2
DO pin voltage "H"	V _{DOH}	CMOS output product	5.0	6.0	7.5	V	2
Input Current							
Current consumption during operation	I _{oPE}	V1 = V2 = V3 = V4 = V5 = 3.4 V	-	2.5	7.0	μA	2
V _{Cn} pin current (n = 1, 2, 3, 4)	I _{VC_n}	V1 = V2 = V3 = V4 = V5 = 3.4 V	-1.0	0	1.0	μA	2
Output Current							
DO pin sink current	I _{DOL}	-	20	-	-	μA	2
DO pin source current	I _{DOH}	CMOS output product	-	-	-20	μA	2
DO pin leakage current	I _{DOLL}	Nch open-drain output product	-	-	0.1	μA	2
CO pin sink current	I _{COL}	-	20	-	-	μA	2
CO pin source current	I _{COH}	CMOS output product	-	-	-20	μA	2
CO pin leakage current	I _{COLL}	Nch open-drain output product	-	-	0.1	μA	2
Delay Time							
Overcharge detection delay time	t _{CU}	-	t _{CU} × 0.7	t _{CU}	t _{CU} × 1.3	-	2
Overdischarge detection delay time	t _{DL}	-	t _{DL} × 0.7	t _{DL}	t _{DL} × 1.3	-	2

*1. Since products are not screened at high and low temperature, the specification for this temperature range is guaranteed by design, not tested in production.

■ **Test Circuits**

Set the initial status of the test circuit as follows.

Table 8

Test Items	CO Pin Output Form	DO Pin Output Form	SW1	SW2	SW3	SW4	SW5	SW6
Current consumption during operation, CO pin sink current, CO pin leakage current, DO pin sink current, DO pin leakage current	-	-	OFF	OFF	OFF	OFF	OFF	OFF
Other than the above	CMOS output	CMOS output	OFF	OFF	OFF	OFF	OFF	OFF
	CMOS output	Nch open-drain output	ON	OFF	OFF	OFF	OFF	OFF
	Nch open-drain output	CMOS output	OFF	ON	OFF	OFF	OFF	OFF
	Nch open-drain output	Nch open-drain output	ON	ON	OFF	OFF	OFF	OFF

1. Overcharge detection voltage n (V_{CU_n})
(Test circuit 1)

After setting $V1 = V2 = V3 = V4 = V5 = V_{CU} - 0.1 V$, $V1$ is gradually increased. When the CO pin output inverts, the voltage $V1$ is defined as the overcharge detection voltage 1 (V_{CU1}). Other overcharge detection voltage n (V_{CU_n}) can be determined in the same way as when $n = 1$.

2. Overcharge release voltage n (V_{CL_n})
(Test circuit 2)

Set $V1 = V_{CU} + 0.1 V$, $V2 = V3 = V4 = V5 = V_{CL} - 0.1 V$ and invert the CO pin output. After that, $V1$ is gradually decreased. When the CO pin output inverts again, the voltage $V1$ is defined as the overcharge release voltage (V_{CL1}). Other overcharge release voltage n (V_{CL_n}) can be determined in the same way as when $n = 1$.

3. Overdischarge detection voltage n (V_{DL_n}), overdischarge release voltage n (V_{DU_n})
(Test circuit 2)

After setting $V1 = V2 = V3 = V4 = V5 = V_{DL} + 0.1 V$, $V1$ is gradually decreased. When the DO pin output inverts, the voltage $V1$ is defined as the overdischarge detection voltage 1 (V_{DL1}). After that, set $V2 = V3 = V4 = V5 = V_{DU} + 0.15 V$. $V1$ is gradually increased. When the DO pin output inverts again, the voltage $V1$ is defined as overdischarge release voltage 1 (V_{DU1}). Other overdischarge detection voltage n (V_{DL_n}) and overdischarge release voltage n (V_{DU_n}) can be determined in the same way as when $n = 1$.

Remark n = 1, 2, 3, 4, 5

**4. CO pin output voltage "H" (V_{COH}), DO pin output voltage "H" (V_{DOH})
(Test circuit 2)**

4.1 CO pin output logic active "H"

The CO pin output voltage "H" (V_{COH}) is the voltage between the CO pin and the VSS pin when setting $V1 = 4.8\text{ V}$, $V2 = V3 = V4 = V5 = 3.05\text{ V}$, $I2 = 0.1\text{ }\mu\text{A}$ and SW6 ON.

4.2 CO pin output logic active "L"

The CO pin output voltage "H" (V_{COH}) is the voltage between the CO pin and the VSS pin when setting $V1 = V2 = V3 = V4 = V5 = 3.4\text{ V}$, $I2 = 0.1\text{ }\mu\text{A}$ and SW6 ON.

4.3 DO pin output logic active "H"

The DO pin output voltage "H" (V_{DOH}) is the voltage between the DO pin and the VSS pin when setting $V1 = 1.4\text{ V}$, $V2 = V3 = V4 = V5 = 3.9\text{ V}$, $I1 = 0.1\text{ }\mu\text{A}$ and SW5 ON.

4.4 DO pin output logic active "L"

The DO pin output voltage "H" (V_{DOH}) is defined as the voltage between the DO pin and the VSS pin when setting $V1 = V2 = V3 = V4 = V5 = 3.4\text{ V}$, $I1 = 0.1\text{ }\mu\text{A}$ and SW5 ON.

**5. CO pin source current (I_{COH}), CO pin sink current (I_{COL}), CO pin leakage current (I_{COLL}),
DO pin source current (I_{DOH}), DO pin sink current (I_{DOL}), DO pin leakage current (I_{DOLL})
(Test circuit 2)**

5.1 CO pin CMOS output product

5.1.1 CO pin output logic active "H"

Set SW4 to ON after setting $V1 = 4.8\text{ V}$, $V2 = V3 = V4 = V5 = 3.05\text{ V}$, $V7 = V_{COH} - 0.5\text{ V}$. The CO pin current is the CO pin source current (I_{COH}) at that time.

Set SW4 to ON after setting $V1 = V2 = V3 = V4 = V5 = 3.4\text{ V}$, $V7 = 0.5\text{ V}$. The CO pin current is the CO pin sink current (I_{COL}) at that time.

5.1.2 CO pin output logic active "L"

Set SW4 to ON after setting $V1 = V2 = V3 = V4 = V5 = 3.4\text{ V}$, $V7 = V_{COH} - 0.5\text{ V}$. The CO pin current is the CO pin source current (I_{COH}) at that time.

Set SW4 to ON after setting $V1 = 4.8\text{ V}$, $V2 = V3 = V4 = V5 = 3.05\text{ V}$, $V7 = 0.5\text{ V}$. The CO pin current is the CO pin sink current (I_{COL}) at that time.

5.2 CO pin Nch open-drain output Product

5.2.1 CO pin output logic active "H"

Set SW4 to ON after setting $V1 = 4.8\text{ V}$, $V2 = V3 = V4 = V5 = 3.05\text{ V}$, $V7 = 17\text{ V}$. The CO pin current is the CO pin leakage current (I_{COLL}) at this time.

Set SW4 to ON after setting $V1 = V2 = V3 = V4 = V5 = 3.4\text{ V}$, $V7 = 0.5\text{ V}$. The CO pin current is the CO pin sink current (I_{COL}) at that time.

5.2.2 CO pin output logic active "L"

Set SW4 to ON after setting $V1 = V2 = V3 = V4 = V5 = 3.4\text{ V}$, $V7 = 17\text{ V}$. The CO pin current is the CO pin leakage current (I_{COLL}) at this time.

Set SW4 to ON after setting $V1 = 4.8\text{ V}$, $V2 = V3 = V4 = V5 = 3.05\text{ V}$, $V7 = 0.5\text{ V}$. The CO pin current is the CO pin sink current (I_{COL}) at that time.

5.3 DO pin CMOS output product

5.3.1 DO pin output logic active "H"

Set SW3 to ON after setting $V1 = 1.4\text{ V}$, $V2 = V3 = V4 = V5 = 3.9\text{ V}$, $V6 = V_{\text{DOH}} - 0.5\text{ V}$. The DO pin current is the DO pin source current (I_{DOH}) at this time.

Set SW3 to ON after setting $V1 = 4.8\text{ V}$, $V2 = 4.1\text{ V}$, $V3 = 4.1\text{ V}$, $V4 = 4.0\text{ V}$, $V5 = 0\text{ V}$, $V6 = 0.5\text{ V}$. The DO pin current is the DO pin sink current (I_{DOL}) at this time.

5.3.2 DO pin output logic active "L"

Set SW3 to ON after setting $V1 = V2 = V3 = V4 = V5 = 3.4\text{ V}$, $V6 = V_{\text{DOH}} - 0.5\text{ V}$. The DO pin current is the DO pin source current (I_{DOH}) at this time.

Set SW3 to ON after setting $V1 = 1.4\text{ V}$, $V2 = V3 = V4 = V5 = 3.9\text{ V}$, $V6 = 0.5\text{ V}$. The DO pin current is the DO pin sink current (I_{DOL}) at this time.

5.4 DO pin Nch open-drain output product

5.4.1 DO pin output logic active "H"

Set SW3 to ON after setting $V1 = 1.4\text{ V}$, $V2 = V3 = V4 = V5 = 3.9\text{ V}$, $V6 = 17\text{ V}$. The DO pin current is the DO pin leak current (I_{DOLL}) at this time.

Set SW3 to ON after setting $V1 = V2 = V3 = V4 = V5 = 3.4\text{ V}$, $V6 = 0.5\text{ V}$. The DO pin current is the DO pin sink current (I_{DOL}) at this time.

5.4.2 DO pin output logic active "L"

Set SW3 to ON after setting $V1 = V2 = V3 = V4 = V5 = 3.4\text{ V}$, $V6 = 17\text{ V}$. The DO pin current is the DO pin leak current (I_{DOLL}) at this time.

Set SW3 to ON after setting $V1 = 1.4\text{ V}$, $V2 = V3 = V4 = V5 = 3.9\text{ V}$, $V6 = 0.5\text{ V}$. The DO pin current is the DO pin sink current (I_{DOL}) at this time.

6. Overcharge detection delay time (t_{CU}) (Test circuit 2)

After setting $V5 = V_{\text{CU}} - 0.2\text{ V}$, $V1 = V2 = V3 = V4 = 3.4\text{ V}$, $V5$ is increased to $V_{\text{CU}} + 0.2\text{ V}$. The overcharge detection delay time (t_{CU}) is the time period until the CO pin output inverts.

7. Overdischarge detection delay time (t_{DL}) (Test circuit 2)

After setting $V5 = V_{\text{DL}} + 0.2\text{ V}$, $V2 = V3 = V4 = V5 = 3.4\text{ V}$, $V5$ is decreased to $V_{\text{DL}} - 0.2\text{ V}$. The overdischarge detection delay time (t_{DL}) is the time period until the DO pin output inverts.

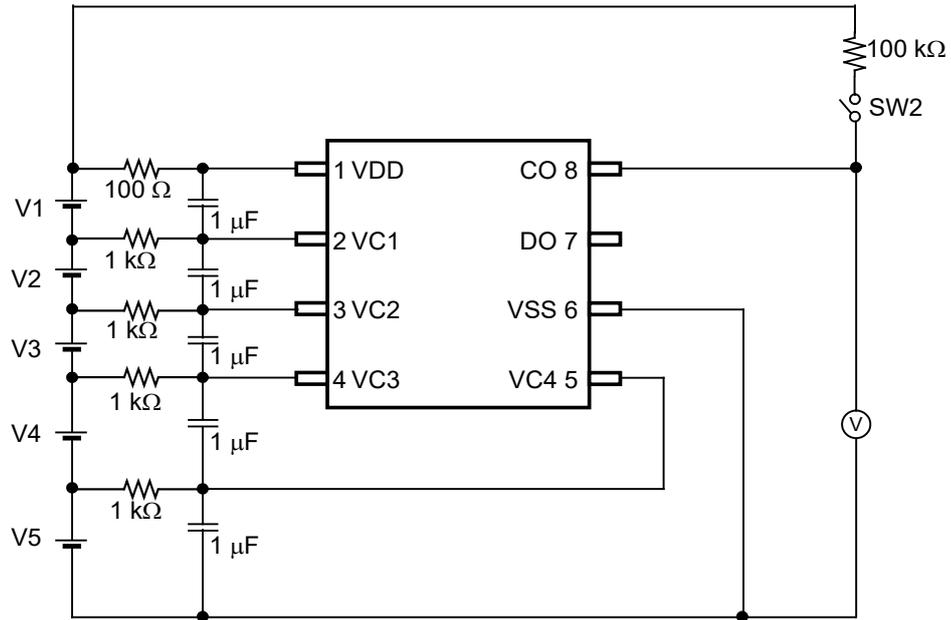


Figure 5 Test Circuit 1

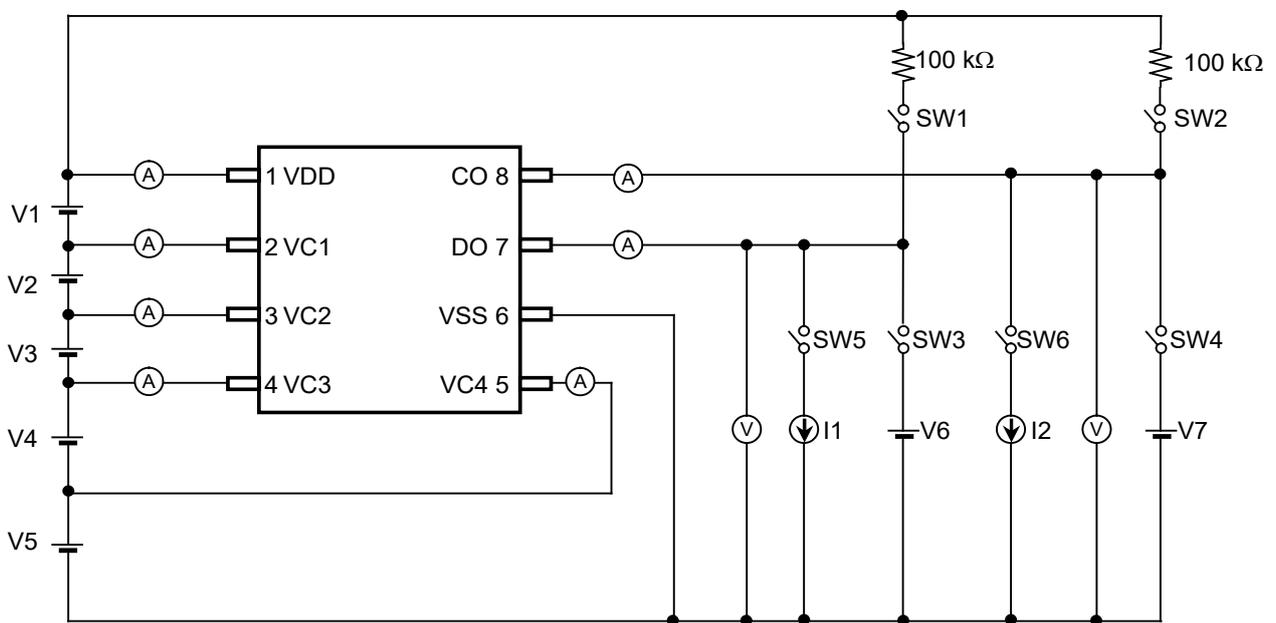


Figure 6 Test Circuit 2

■ **Operation**

1. Normal status

When the voltage of all batteries is in the range between the overdischarge detection voltage n (V_{DLn}) and the overcharge detection voltage (V_{CUn}), the CO pin output is shown in **Table 9**, and the DO pin output is shown in **Table 10**. This status is called the normal status.

Table 9

CO Pin Output Logic	CO Pin Output
Active "H"	"L"
Active "L"	"H"

Table 10

DO Pin Output Logic	DO Pin Output
Active "H"	"L"
Active "L"	"H"

2. Overcharge status

When the voltage of any of the batteries exceeds the overcharge detection voltage n (V_{CUn}) during charging and this condition continues for the overcharge detection delay time (t_{CU}) or longer, the CO pin output inverts. This status is called the overcharge status.

When the voltage of all batteries falls below the overcharge release voltage n (V_{CLn}), the overcharge status is released, and this IC returns to its normal status.

3. Overdischarge status

When the voltage of any of the batteries falls below the overdischarge detection voltage n (V_{DLn}) during discharging and the status continues for the overdischarge detection delay time (t_{DL}) or longer, the DO pin output inverts. This status is called the overdischarge status.

When the voltage of all batteries becomes overdischarge release voltage n (V_{DU_n}) or higher, this IC returns to normal status.

Remark $n = 1, 2, 3, 4, 5$

4. Test mode

In this IC, the overcharge detection delay time (t_{CU}) and the overdischarge delay time (t_{DL}) can be shortened by entering the test mode.

This IC transitions to the test mode by setting the DO pin voltage to the following voltage while the IC is in the normal status.

Table 11

DO Pin Output Form	DO Pin Output Logic	DO Pin Voltage
CMOS output	Active "L"	0 V
CMOS output	Active "H"	5 V
Nch open-drain output	–	$V_{DD} + 5 V$

In the test mode, overdischarge status output is output from the CO pin, not the DO pin.

After transitioning to the test mode, the test mode is retained even if this IC transitions to the overcharge status or the overdischarge status by retaining the DO pin voltage.

The test mode is released when the DO pin voltage input is returned to normal status output.

Caution Set the test mode when all batteries are neither overcharged nor overdischarged.

5. VCn pin

The VCn pin is connected to a constant current circuit. When the connection between the battery and the IC is disconnected, pulling up/down the VCn pin using this constant current circuit enables disconnection detection.

However, this disconnection detection may not work properly due to other external components.

If detection operation is required, please conduct thorough evaluations with the actual applications. If this constant current circuit is not required, select the S-82H5A Series.

Remark n = 1, 2, 3, 4

■ Timing Charts

1. Overcharge detection operation

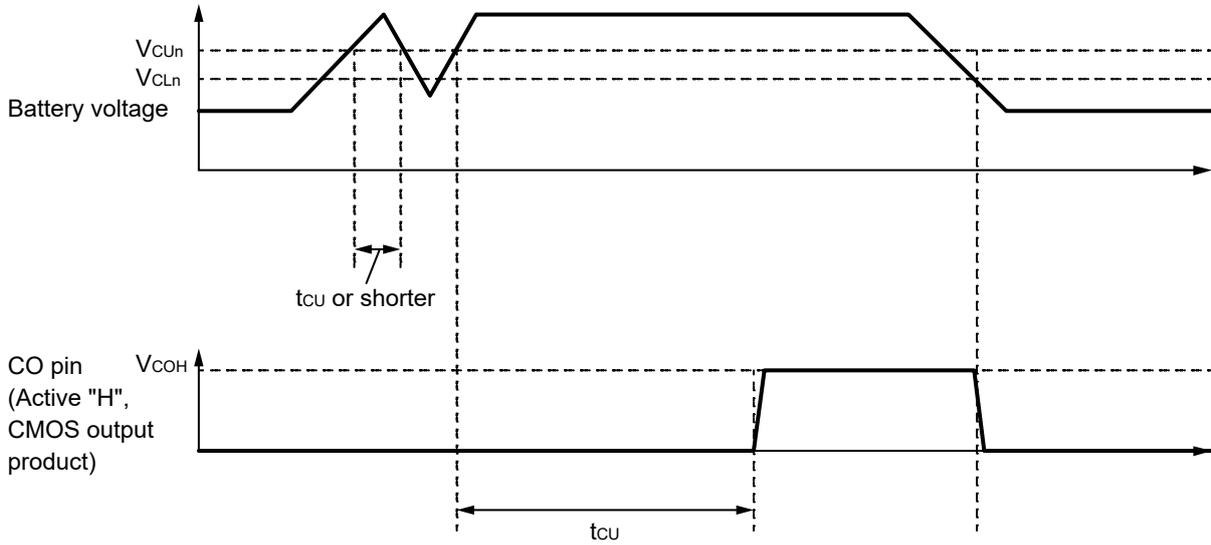


Figure 7

2. Overdischarge detection operation

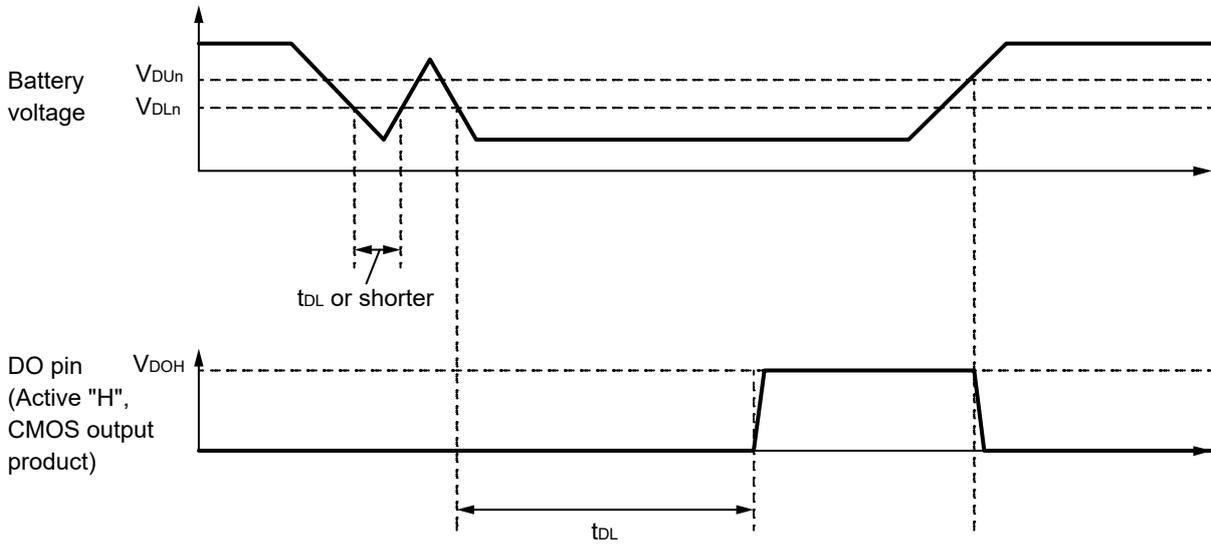


Figure 8

Remark n = 1, 2, 3, 4, 5

■ **Connection Examples of Battery Monitoring IC**

1. 5-serial cell (CO pin output form: CMOS output, DO pin output form: CMOS output)

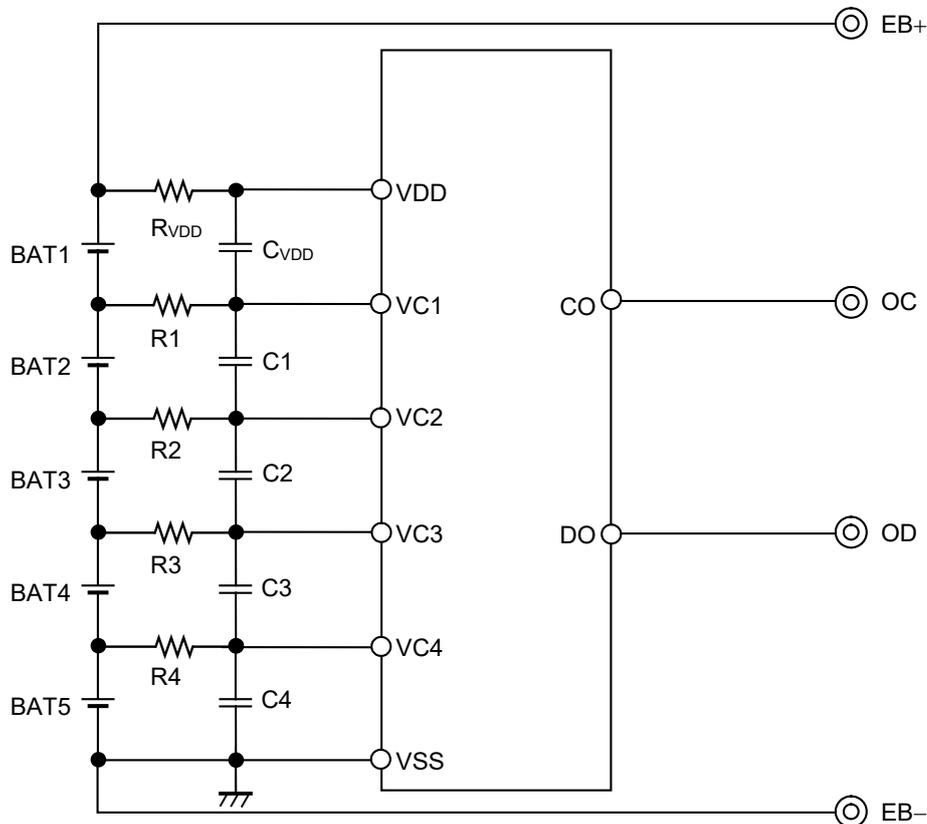


Figure 9

Table 12 Constants for External Components

No.	Part	Typ.	Unit
1	R1 to R4	1	kΩ
2	C1 to C4, CvDD	1	μF
3	RvDD	100	Ω

- Caution**
1. The constants may be changed without notice.
 2. It has not been confirmed whether the operation is normal or not in circuits other than the connection example. In addition, the connection example and the constants do not guarantee proper operation. Perform thorough evaluation using the actual application to set the constants.

2. 4-serial cell (CO pin output form: CMOS output, DO pin output form: CMOS output)

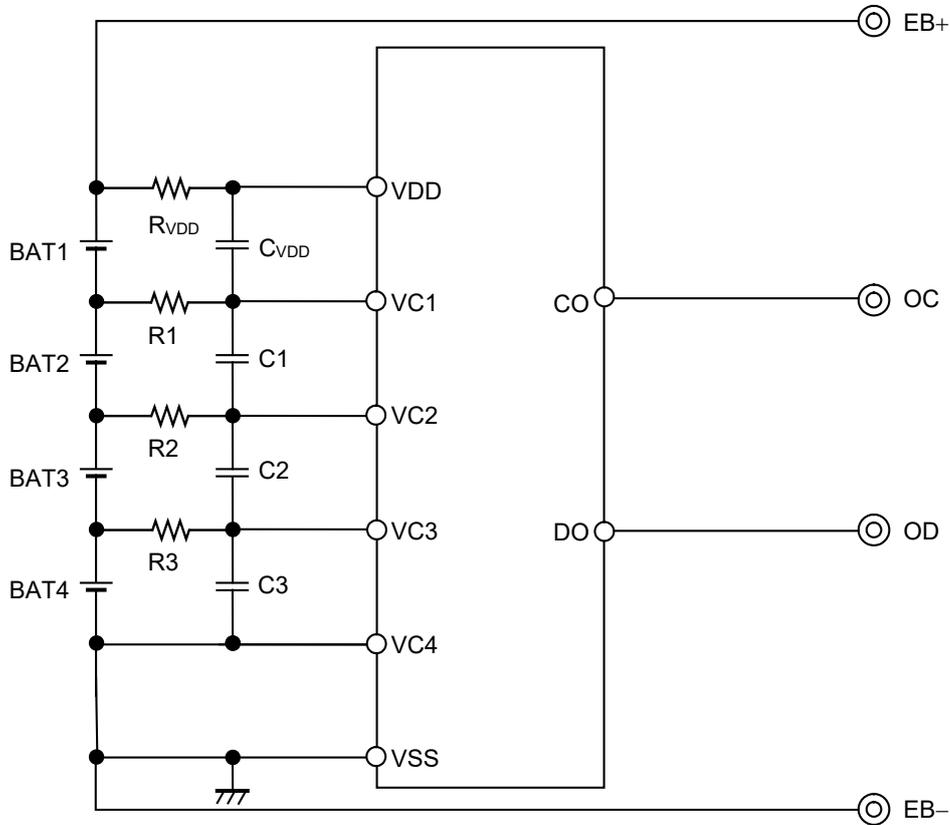


Figure 10

Table 13 Constants for External Components

No.	Part	Typ.	Unit
1	R1 to R3	1	kΩ
2	C1 to C3, C _{VDD}	1	μF
3	R _{VDD}	100	Ω

- Caution**
1. The constants may be changed without notice.
 2. It has not been confirmed whether the operation is normal or not in circuits other than the connection example. In addition, the connection example and the constants do not guarantee proper operation. Perform thorough evaluation using the actual application to set the constants.

3. 3-serial cell (CO pin output form: CMOS output, DO pin output form: CMOS output)

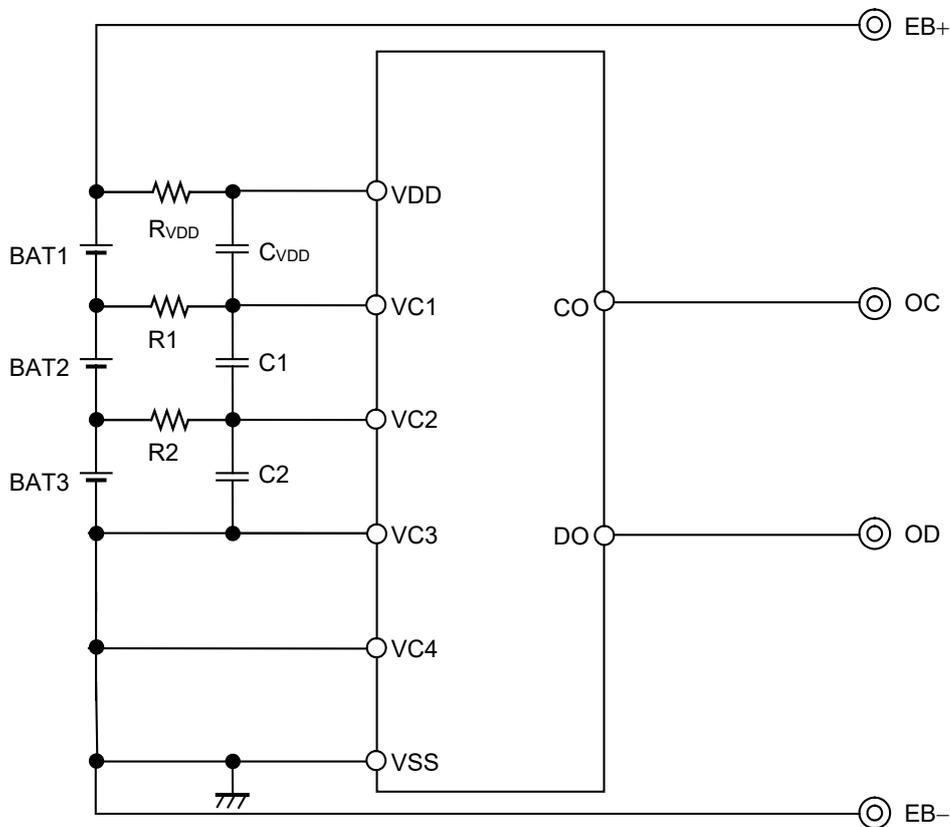


Figure 11

Table 14 Constants for External Components

No.	Part	Typ.	Unit
1	R1, R2	1	kΩ
2	C1, C2, CVDD	1	μF
3	RVDD	100	Ω

- Caution**
1. The constants may be changed without notice.
 2. It has not been confirmed whether the operation is normal or not in circuits other than the connection example. In addition, the connection example and the constants do not guarantee proper operation. Perform thorough evaluation using the actual application to set the constants.

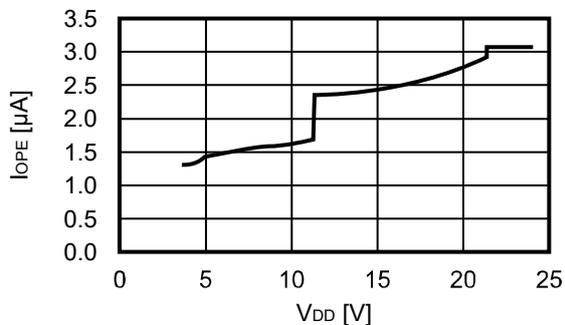
■ Precautions

- The application conditions for the input voltage, output voltage, and load current should not exceed the power dissipation.
- If an overcharged battery and an overdischarged battery intermix, this IC will change to the overcharge and overdischarge statuses.
- Do not apply an electrostatic discharge to this IC that exceeds the performance ratings of the built-in electrostatic protection circuit.
- ABLIC Inc. claims no responsibility for any and all disputes arising out of or in connection with any infringement by products including this IC of patents owned by a third party.

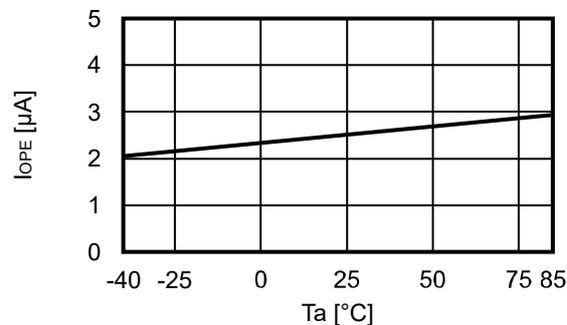
■ **Characteristics (Typical Data)**

1. Current consumption

1.1 I_{OPE} vs. V_{DD}

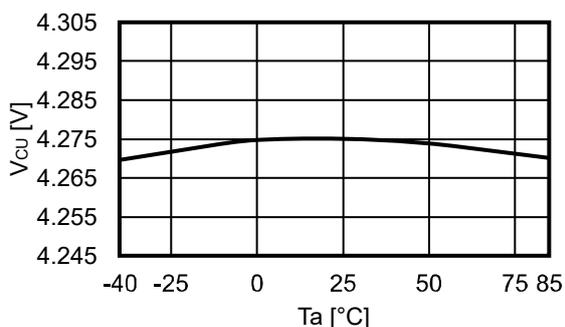


1.2 I_{OPE} vs. T_a

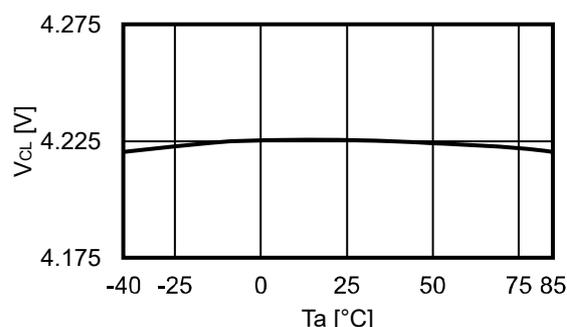


2. Detection voltage, release voltage

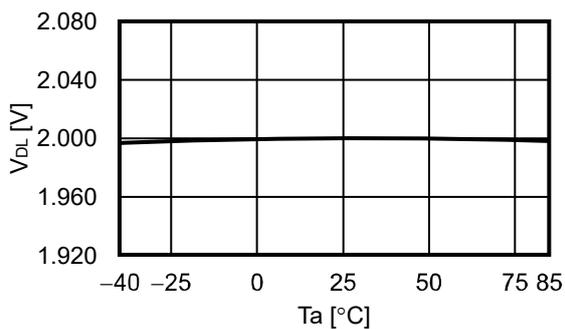
2.1 V_{Cu} vs. T_a



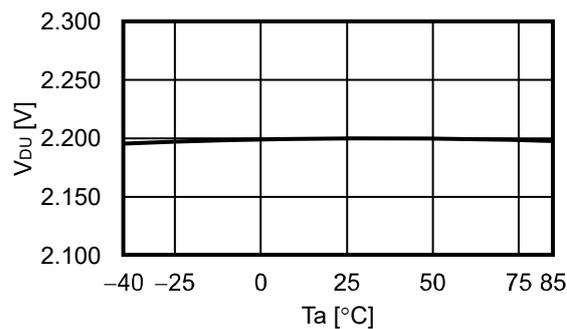
2.2 V_{CL} vs. T_a



2.3 V_{DL} vs. T_a

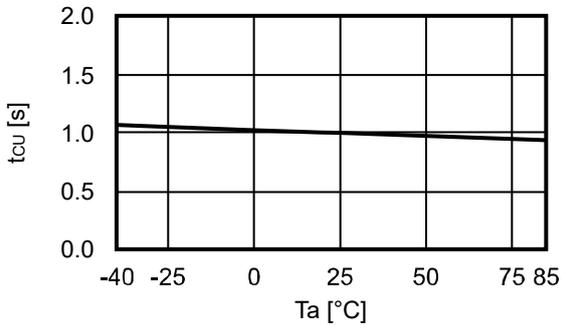


2.4 V_{DU} vs. T_a

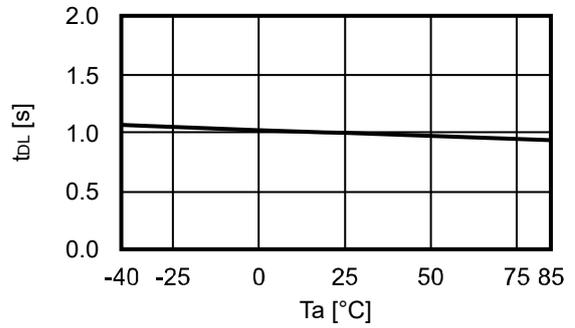


3. Delay time

3.1 t_{CU} vs. T_a

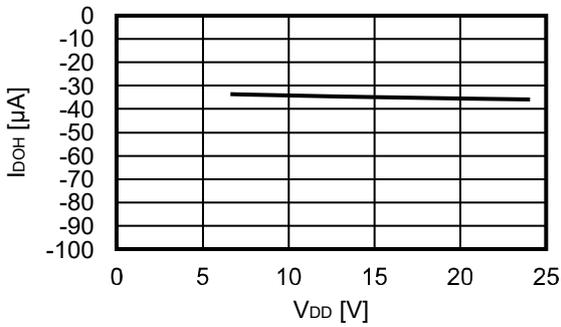


3.2 t_{DL} vs. T_a

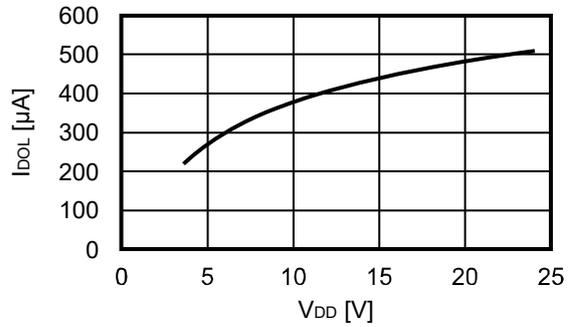


4. Output pin

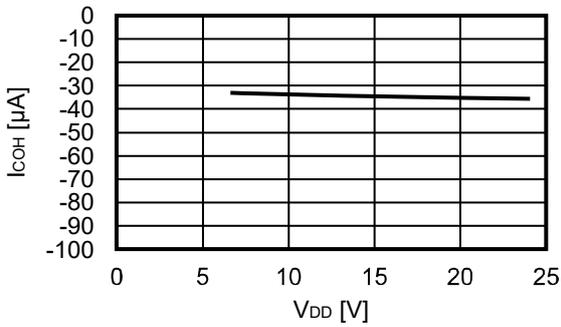
4.1 I_{DOH} vs. V_{DD}



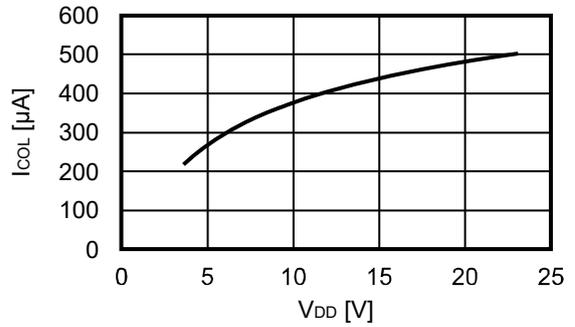
4.2 I_{DOL} vs. V_{DD}



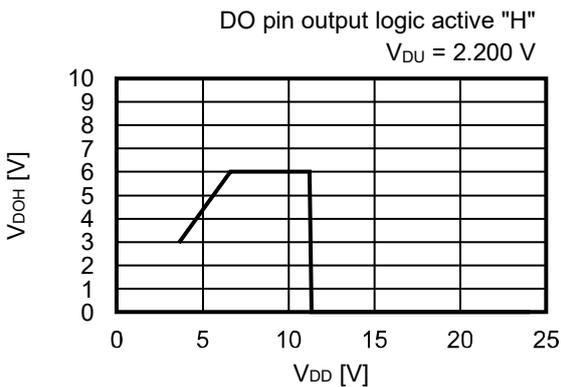
4.3 I_{COH} vs. V_{DD}



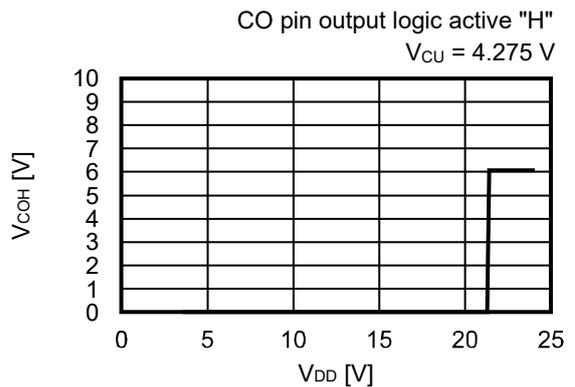
4.4 I_{COL} vs. V_{DD}



4.5 V_{DOH} vs. V_{DD}

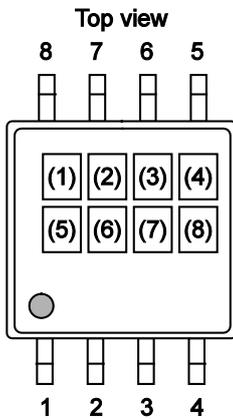


4.6 V_{COH} vs. V_{DD}



■ **Marking Specifications**

1. **TMSOP-8**

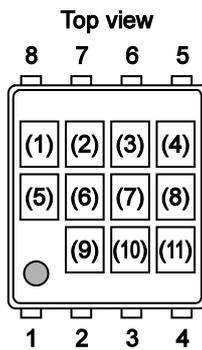


- (1): Blank
- (2) to (4): Product code (refer to **Product name vs. Product code**)
- (5): Blank
- (6) to (8): Lot number

Product name vs. Product code

Product Name	Product Code		
	(2)	(3)	(4)
S-82H5BAA-K8T2U	9	V	A

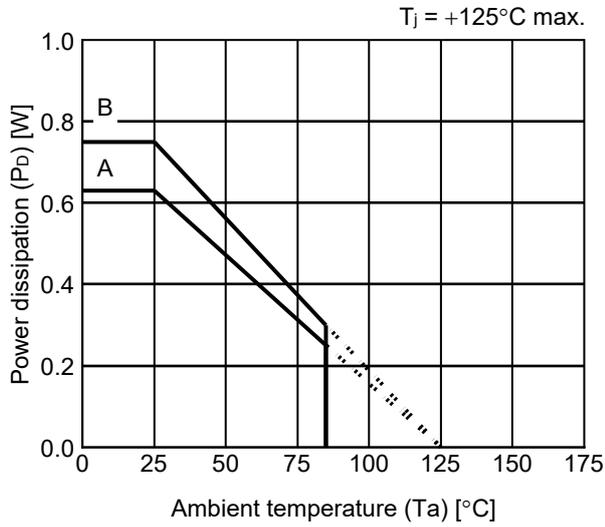
2. **SNT-8A**



- (1): Blank
- (2) to (4): Product code
- (5), (6): Blank
- (7) to (11): Lot number

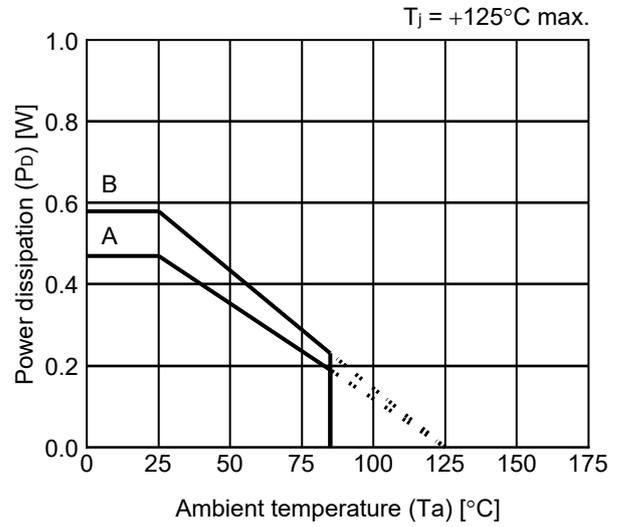
■ **Power Dissipation**

TMSOP-8



Board	Power Dissipation (P _D)
A	0.63 W
B	0.75 W
C	–
D	–
E	–

SNT-8A

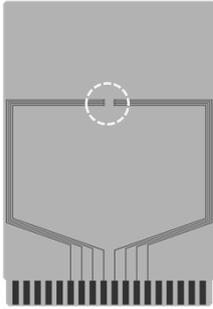


Board	Power Dissipation (P _D)
A	0.47 W
B	0.58 W
C	–
D	–
E	–

TMSOP-8 Test Board

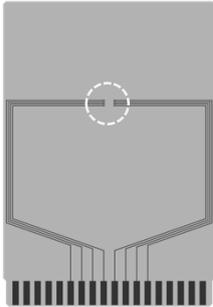
(1) Board A

 IC Mount Area



Item	Specification	
Size [mm]	114.3 x 76.2 x t1.6	
Material	FR-4	
Number of copper foil layer	2	
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	-
	3	-
	4	74.2 x 74.2 x t0.070
Thermal via	-	

(2) Board B



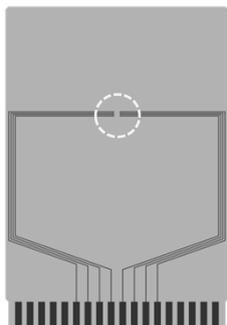
Item	Specification	
Size [mm]	114.3 x 76.2 x t1.6	
Material	FR-4	
Number of copper foil layer	4	
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via	-	

No. TMSOP8-A-Board-SD-1.0

SNT-8A Test Board

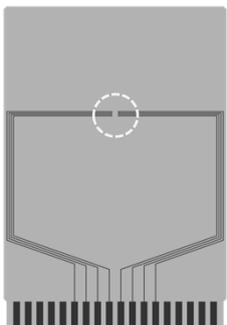
(1) Board A

 IC Mount Area



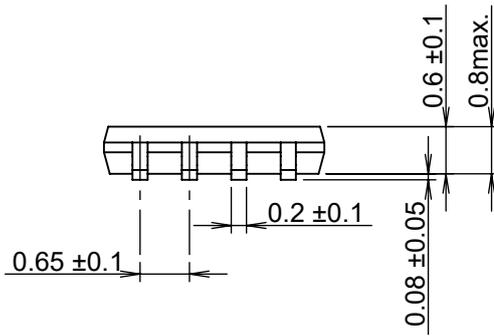
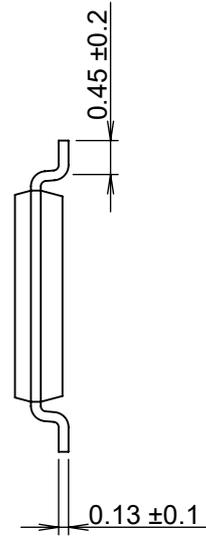
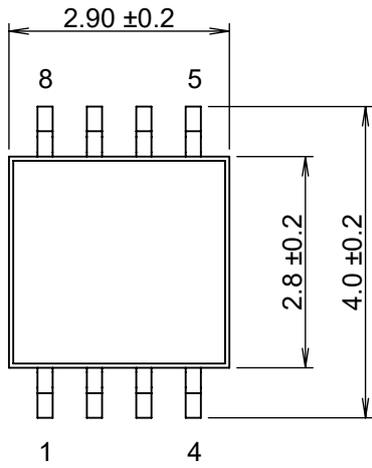
Item	Specification	
Size [mm]	114.3 x 76.2 x t1.6	
Material	FR-4	
Number of copper foil layer	2	
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	-
	3	-
	4	74.2 x 74.2 x t0.070
Thermal via	-	

(2) Board B



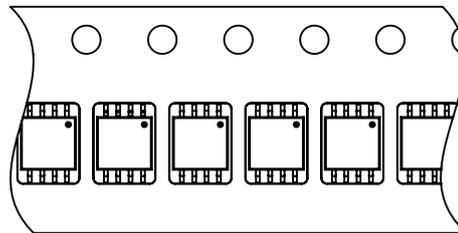
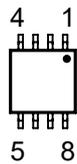
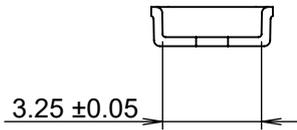
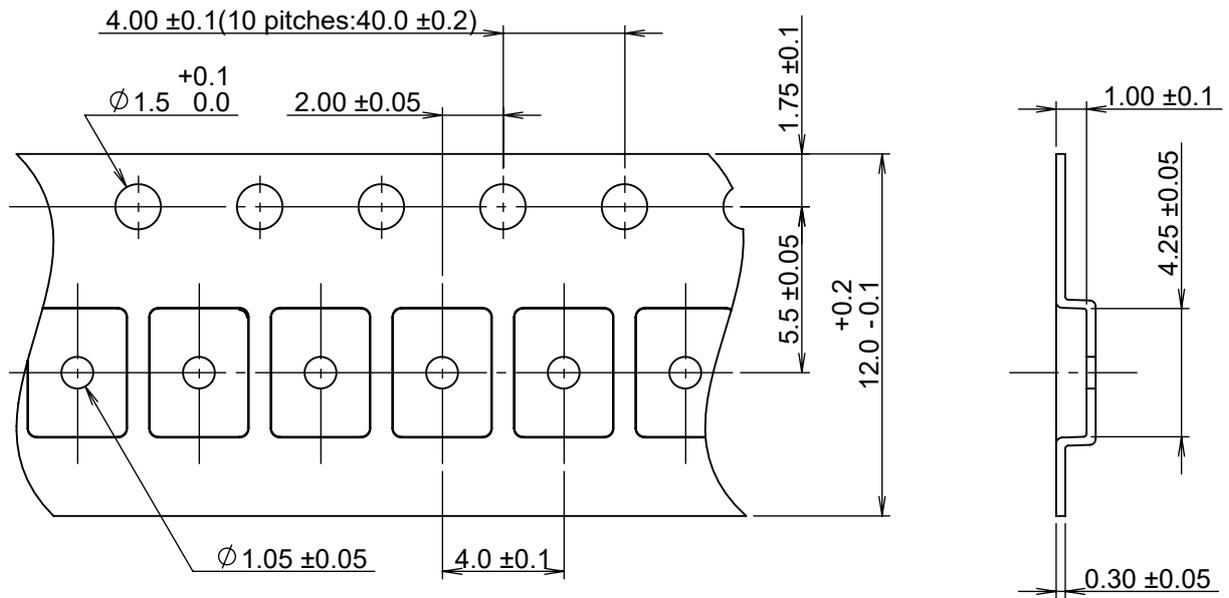
Item	Specification	
Size [mm]	114.3 x 76.2 x t1.6	
Material	FR-4	
Number of copper foil layer	4	
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via	-	

No. SNT8A-A-Board-SD-1.0



No.FM008-A-P-SD-1.2

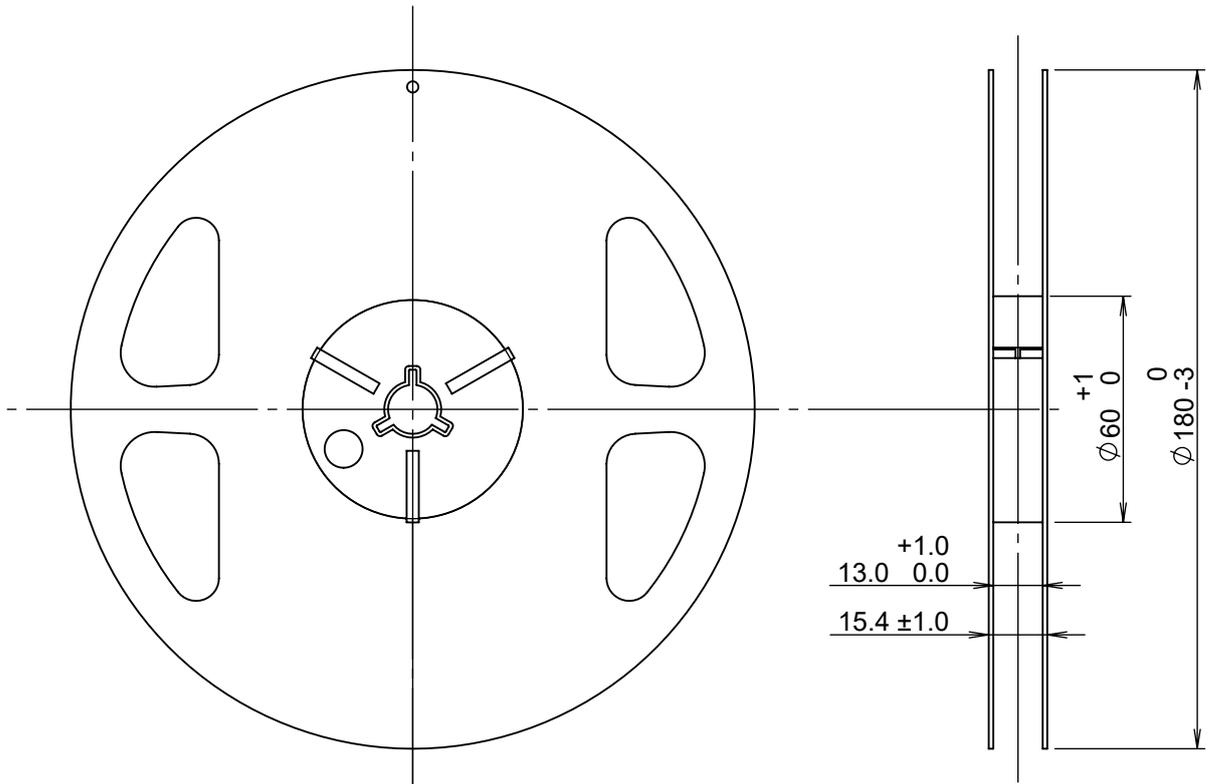
TITLE	TMSOP8-A-PKG Dimensions
No.	FM008-A-P-SD-1.2
ANGLE	
UNIT	mm
ABLIC Inc.	



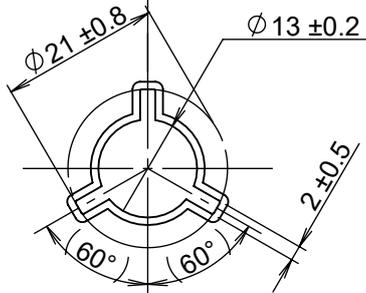
→
Feed direction

No. FM008-A-C-SD-3.0

TITLE	TMSOP8-A-Carrier Tape
No.	FM008-A-C-SD-3.0
ANGLE	
UNIT	mm
ABLIC Inc.	

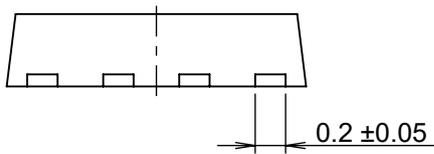
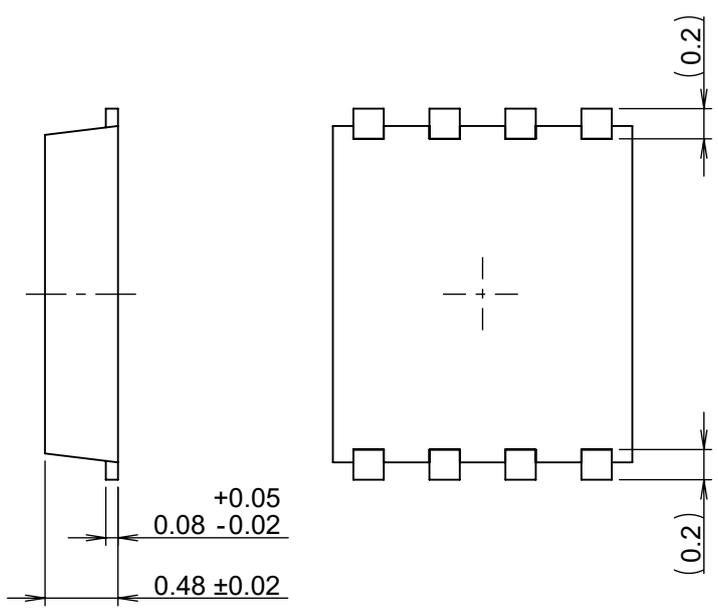
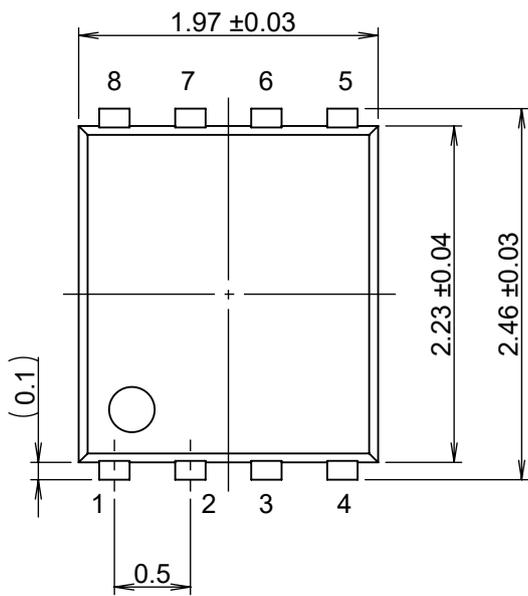


Enlarged drawing in the central part



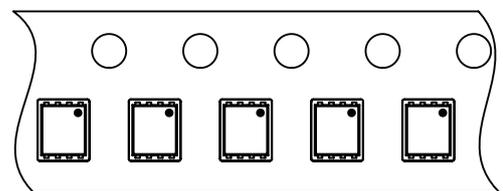
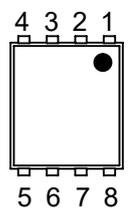
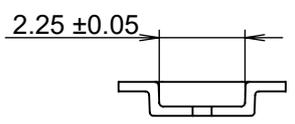
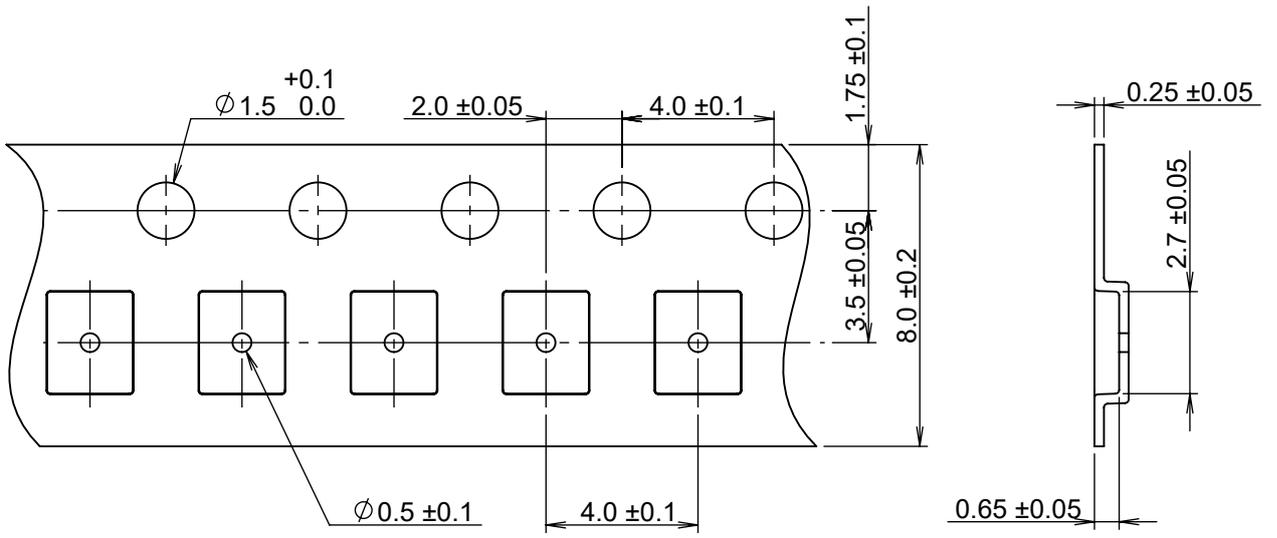
No. FM008-A-R-SD-2.0

TITLE	TMSOP8-A-Reel		
No.	FM008-A-R-SD-2.0		
ANGLE		QTY.	4,000
UNIT	mm		
ABLIC Inc.			



No. PH008-A-P-SD-2.1

TITLE	SNT-8A-A-PKG Dimensions
No.	PH008-A-P-SD-2.1
ANGLE	
UNIT	mm
ABLIC Inc.	

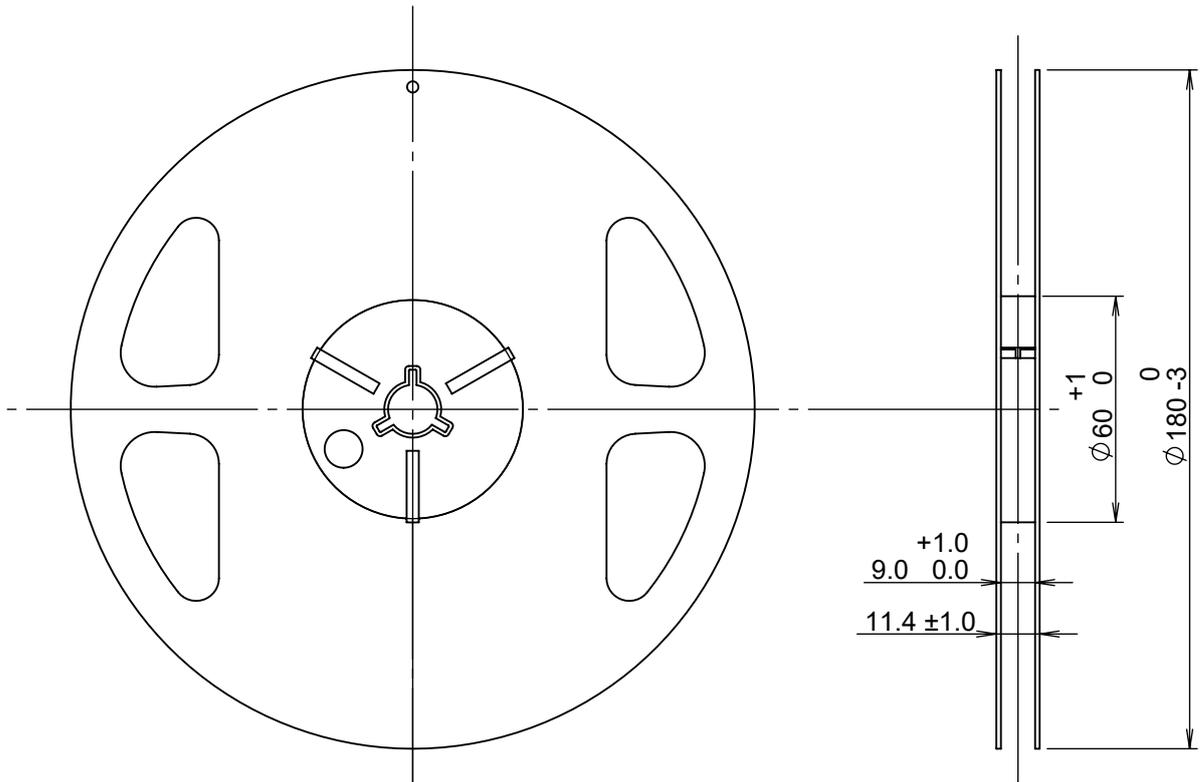


→
Feed direction

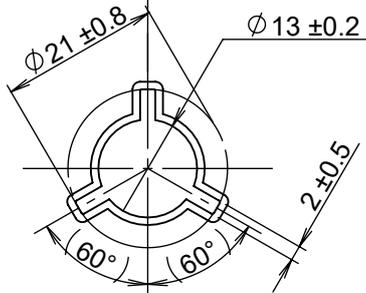
No. PH008-A-C-SD-2.0

TITLE	SNT-8A-A-Carrier Tape
No.	PH008-A-C-SD-2.0
ANGLE	
UNIT	mm

ABLIC Inc.

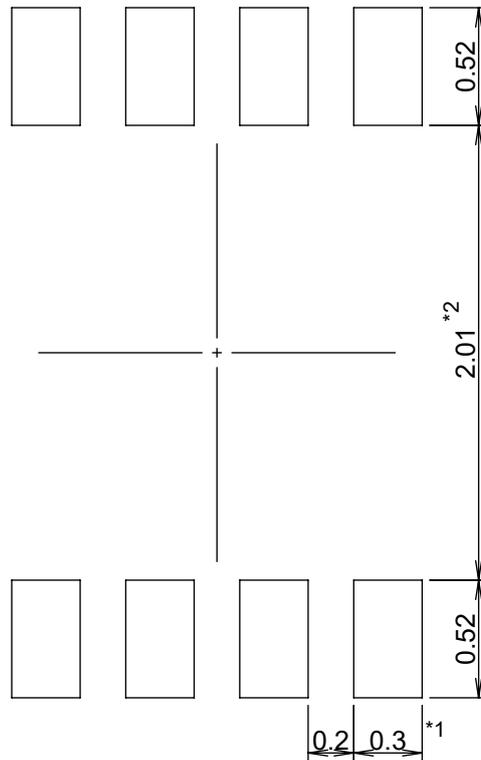


Enlarged drawing in the central part



No. PH008-A-R-SD-2.0

TITLE	SNT-8A-A-Reel		
No.	PH008-A-R-SD-2.0		
ANGLE		QTY.	5,000
UNIT	mm		
ABLIC Inc.			



- *1. ランドパターンの幅に注意してください (0.25 mm min. / 0.30 mm typ.).
- *2. パッケージ中央にランドパターンを広げないでください (1.96 mm ~ 2.06 mm)。

- 注意 1. パッケージのモールド樹脂下にシルク印刷やハンダ印刷などしないでください。
 2. パッケージ下の配線上のソルダーレジストなどの厚みをランドパターン表面から0.03 mm以下にしてください。
 3. マスク開口サイズと開口位置はランドパターンと合わせてください。
 4. 詳細は "SNTパッケージ活用の手引き" を参照してください。

- *1. Pay attention to the land pattern width (0.25 mm min. / 0.30 mm typ.).
- *2. Do not widen the land pattern to the center of the package (1.96 mm to 2.06 mm).

- Caution 1. Do not do silkscreen printing and solder printing under the mold resin of the package.**
2. The thickness of the solder resist on the wire pattern under the package should be 0.03 mm or less from the land pattern surface.
3. Match the mask aperture size and aperture position with the land pattern.
4. Refer to "SNT Package User's Guide" for details.

- *1. 请注意焊盘模式的宽度 (0.25 mm min. / 0.30 mm typ.).
- *2. 请勿向封装中间扩展焊盘模式 (1.96 mm ~ 2.06 mm)。

- 注意 1. 请勿在树脂型封装的下面印刷丝网、焊锡。
 2. 在封装下、布线上的阻焊膜厚度 (从焊盘模式表面起) 请控制在0.03 mm以下。
 3. 钢网的开口尺寸和开口位置请与焊盘模式对齐。
 4. 详细内容请参阅 "SNT封装的应用指南"。

No. PH008-A-L-SD-4.1

TITLE	SNT-8A-A -Land Recommendation
No.	PH008-A-L-SD-4.1
ANGLE	
UNIT	mm
ABLIC Inc.	

Disclaimers (Handling Precautions)

1. All the information described herein (product data, specifications, figures, tables, programs, algorithms and application circuit examples, etc.) is current as of publishing date of this document and is subject to change without notice.
2. The circuit examples and the usages described herein are for reference only, and do not guarantee the success of any specific mass-production design.
ABLIC Inc. is not liable for any losses, damages, claims or demands caused by the reasons other than the products described herein (hereinafter "the products") or infringement of third-party intellectual property right and any other right due to the use of the information described herein.
3. ABLIC Inc. is not liable for any losses, damages, claims or demands caused by the incorrect information described herein.
4. Be careful to use the products within their ranges described herein. Pay special attention for use to the absolute maximum ratings, operation voltage range and electrical characteristics, etc.
ABLIC Inc. is not liable for any losses, damages, claims or demands caused by failures and / or accidents, etc. due to the use of the products outside their specified ranges.
5. Before using the products, confirm their applications, and the laws and regulations of the region or country where they are used and verify suitability, safety and other factors for the intended use.
6. When exporting the products, comply with the Foreign Exchange and Foreign Trade Act and all other export-related laws, and follow the required procedures.
7. The products are strictly prohibited from using, providing or exporting for the purposes of the development of weapons of mass destruction or military use. ABLIC Inc. is not liable for any losses, damages, claims or demands caused by any provision or export to the person or entity who intends to develop, manufacture, use or store nuclear, biological or chemical weapons or missiles, or use any other military purposes.
8. The products are not designed to be used as part of any device or equipment that may affect the human body, human life, or assets (such as medical equipment, disaster prevention systems, security systems, combustion control systems, infrastructure control systems, vehicle equipment, traffic systems, in-vehicle equipment, aviation equipment, aerospace equipment, and nuclear-related equipment), excluding when specified for in-vehicle use or other uses by ABLIC, Inc. Do not apply the products to the above listed devices and equipments.
ABLIC Inc. is not liable for any losses, damages, claims or demands caused by unauthorized or unspecified use of the products.
9. In general, semiconductor products may fail or malfunction with some probability. The user of the products should therefore take responsibility to give thorough consideration to safety design including redundancy, fire spread prevention measures, and malfunction prevention to prevent accidents causing injury or death, fires and social damage, etc. that may ensue from the products' failure or malfunction.
The entire system in which the products are used must be sufficiently evaluated and judged whether the products are allowed to apply for the system on customer's own responsibility.
10. The products are not designed to be radiation-proof. The necessary radiation measures should be taken in the product design by the customer depending on the intended use.
11. The products do not affect human health under normal use. However, they contain chemical substances and heavy metals and should therefore not be put in the mouth. The fracture surfaces of wafers and chips may be sharp. Be careful when handling these with the bare hands to prevent injuries, etc.
12. When disposing of the products, comply with the laws and ordinances of the country or region where they are used.
13. The information described herein contains copyright information and know-how of ABLIC Inc. The information described herein does not convey any license under any intellectual property rights or any other rights belonging to ABLIC Inc. or a third party. Reproduction or copying of the information from this document or any part of this document described herein for the purpose of disclosing it to a third-party is strictly prohibited without the express permission of ABLIC Inc.
14. For more details on the information described herein or any other questions, please contact ABLIC Inc.'s sales representative.
15. This Disclaimers have been delivered in a text using the Japanese language, which text, despite any translations into the English language and the Chinese language, shall be controlling.

2.4-2019.07